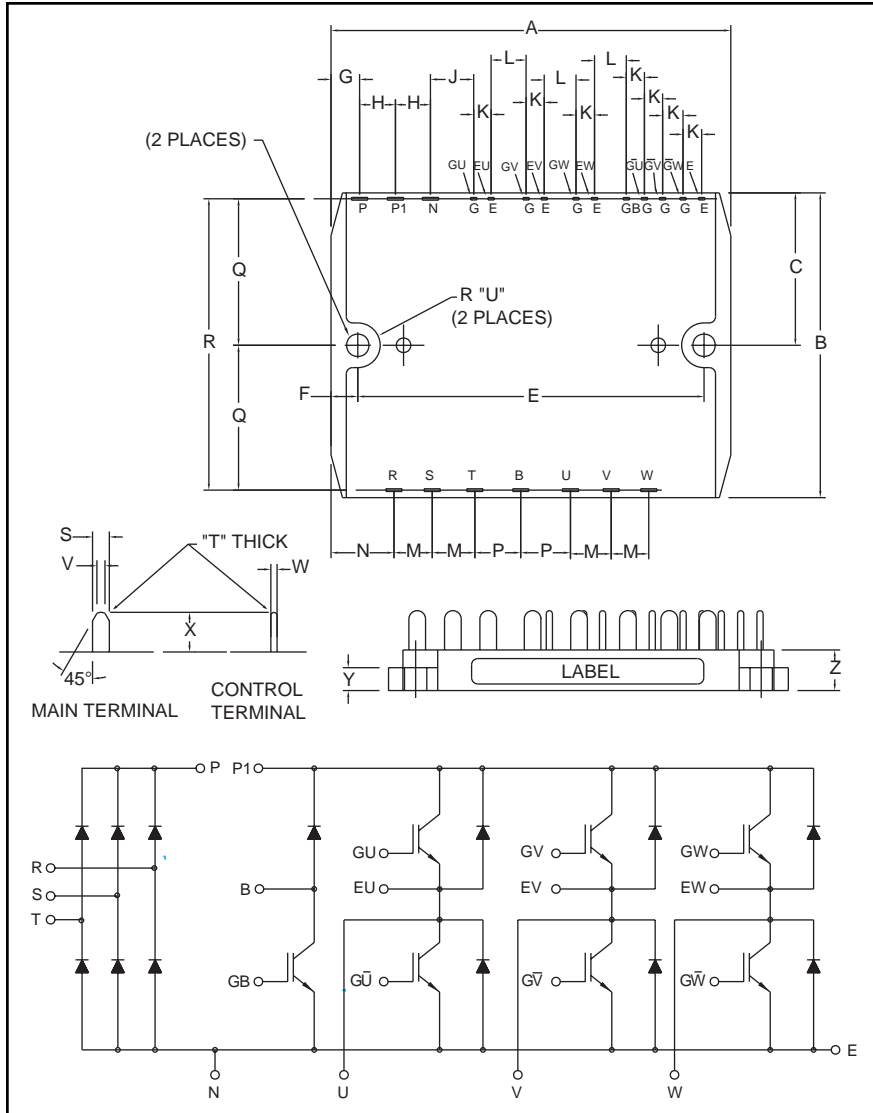


CIB Module

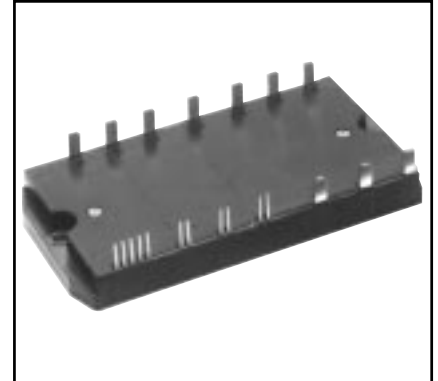
Three Phase Converter +
Three Phase Inverter + Brake
30 Amperes/600 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.53	115.0
B	2.36	60.0
C	1.18	30.0
D	0.18	4.5
E	4.13	105.0
F	0.20	5.0
G	0.31	8.0
H	0.59	15.0
J	0.68	17.2
K	0.10	2.54
L	0.40	10.16
M	0.49	12.5

Dimensions	Inches	Millimeters
N	0.51	13.0
P	0.59	15.0
Q	1.14	29.0
R	2.28	58.0
S	0.16	4.0
T	0.02	0.6
U	0.22	5.5
V	0.08	2.0
W	0.02	0.6
X	0.35	9.0
Y	0.25	6.3
Z	0.47	12.0



Description:

Powerex CIB Modules are designed for use in switching applications. Each module consists of a three phase diode converter section, a three phase IGBT inverter section and a brake section. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- Low Drive Power
- Low $V_{CE(sat)}$
- Discrete Super-Fast Recovery (70ns) Free-Wheel Diodes
- High Frequency Operation (20-25 kHz)
- Isolated Baseplate for Easy Heat Sinking

Applications:

- AC Motor Control
- Motion/Servo Control
- General Purpose Inverters
- Robotics

Ordering Information:

Example: Select the complete nine digit module part number you desire from the table below - i.e. CM30MD-12H is a 600V (V_{CES}), 30 Ampere CIB Power Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	30	12

CM30MD-12H

CIB Module

Three Phase Converter + Three Phase Inverter + Brake

30 Amperes/600 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	CM30MD-12H	Units
Power Device Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^\circ\text{C}$
Mounting Torque, M4 Mounting Screws	—	13	in-lb
Module Weight (Typical)	—	100	Grams
Isolation Voltage, AC 1 minute, 60Hz	V_{RMS}	2500	Volts

Converter Part

Repetitive Peak Reverse Voltage	V_{RRM}	800	Volts
Recommended AC Input Voltage	E_a	220	Volts
DC Output Current	I_o	30	Amperes
Surge (Non-repetitive) Forward Current	I_{FSM}	300	Amperes
I^2t for Fusing	I^2t	375	A^2s

IGBT Inverter Part

Collector-Emitter Voltage (G-E Short)	V_{CES}	600	Volts
Gate-Emitter Voltage (C-E Short)	V_{GES}	± 20	Volts
Collector Current	I_C	30	Amperes
Collector Current (Pulse)*	I_{CM}	60	Amperes
Emitter Current**	I_E	30	Amperes
Emitter Current** (Pulse)*	I_{EM}	60	Amperes
Maximum Collector Dissipation	P_C	66	Watts

Brake Part

Collector-Emitter Voltage (G-E Short)	V_{CES}	600	Volts
Gate-Emitter Voltage (C-E Short)	V_{GES}	± 20	Volts
Collector Current	I_C	30	Amperes
Collector Current (Pulse)*	I_{CM}	60	Amperes
Collector Dissipation	P_C	66	Watts
Repetitive Peak Reverse Voltage (Clamp Diode Part)	V_{RRM}	600	Volts
Forward Current (Clamp Diode Part)	I_{FM}	30	Amperes

* Pulse width and repetition rate should be such that device junction temperature does not exceed maximum rating.

** Characteristics of the anti-parallel emitter-collector free-wheel diode.

CM30MD-12H
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Electrical and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Converter Sector						
Repetitive Reverse Current	I_{RRM}	$V_R = V_{RRM}, T_j = 150^\circ\text{C}$	—	—	8	mA
Forward Voltage Drop	V_{FM}	$I_F = 30\text{A}$	—	—	1.5	Volts
Thermal Resistance (Junction-to-Fin)	$R_{th(j-f)}$	Per Diode	—	—	1.7	$^\circ\text{C/W}$
Brake Sector						
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{V}, I_C = 30\text{A}, T_j = 25^\circ\text{C}$	—	2.1	2.8	Volts
		$V_{GE} = 15\text{V}, I_C = 30\text{A}, T_j = 150^\circ\text{C}$	—	2.15	—	Volts
Collector Cutoff Current	I_{CES}	$V_{CE} = V_{CES}, V_{GE} = 0\text{V}$	—	—	1	mA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 3.0\text{mA}, V_{CE} = 10\text{V}$	4.5	6.0	7.5	Volts
Gate-Emitter Cutoff Current	I_{GES}	$V_{GE} = V_{GES}, V_{CE} = 0\text{V}$	—	—	0.5	μA
Input Capacitance	C_{ies}		—	—	3.0	nF
Output Capacitance	C_{oes}	$V_{GE} = 0\text{V}, V_{CE} = 10\text{V}$	—	—	2.4	nF
Reverse Transfer Capacitance	C_{res}		—	—	0.6	nF
Total Gate Charge	Q_G	$V_{CC} = 300\text{V}, I_C = 30\text{A}, V_{GE} = 15\text{V}$	—	90	—	nC
Forward Voltage Drop	V_{FM}	$I_F = 30\text{A}$	—	—	1.5	Volts
Thermal Resistance (Junction-to-Fin)	$R_{th(j-f)}$	Per IGBT	—	—	1.9	$^\circ\text{C/W}$
		Per Clamp Diode	—	—	1.7	$^\circ\text{C/W}$

CM30MD-12H

CIB Module

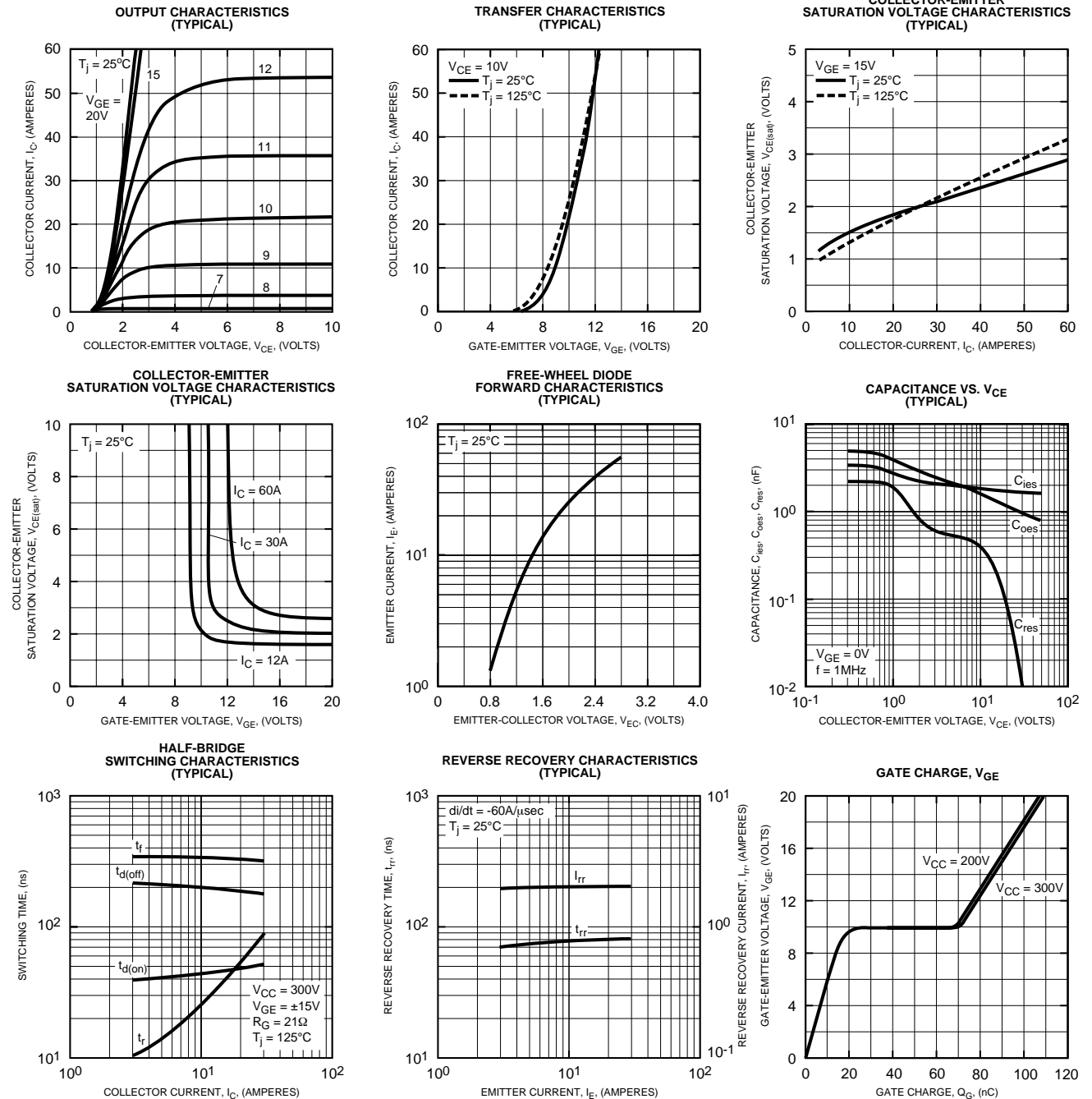
Three Phase Converter + Three Phase Inverter + Brake

30 Amperes/600 Volts

Electrical and Mechanical Characteristics, T_j = 25°C unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units	
IGBT Inverter Sector							
Collector Cutoff Current	I _{CEs}	V _{CE} = V _{CEs} , V _{GE} = 0V	—	—	1	mA	
Gate-Emitter Threshold Voltage	V _{GE(th)}	V _{CE} = 10V, I _C = 3.0mA	4.5	6.0	7.5	Volts	
Gate-Emitter Cutoff Current	I _{GES}	V _{GE} = V _{GES} , V _{CE} = 0V	—	—	0.5	μA	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} = 15V, I _C = 30A, T _j = 25°C	—	2.1	2.8	Volts	
		V _{GE} = 15V, I _C = 30A, T _j = 150°C	—	2.15	—	Volts	
Input Capacitance	C _{ies}		—	—	3.0	nF	
Output Capacitance	C _{oes}	V _{GE} = 0V, V _{CE} = 10V	—	—	2.4	nF	
Reverse Transfer Capacitance	C _{res}		—	—	0.6	nF	
Total Gate Charge	Q _G	V _{CC} = 300V, I _C = 30A, V _{GE} = 15V	—	90	—	nC	
Resistive Load	Turn-on Delay Time	t _{d(on)}	V _{GE1} = V _{GE2} = 15V,		—	120	nS
	Rise Time	t _r	V _{CC} = 300V, I _C = 30A,		—	300	nS
Switching Times	Turn-off Delay Time	t _{d(off)}	R _g = 21Ω,		—	200	nS
	Fall Time	t _f	Resistive Load		—	300	nS
Emitter-Collector Voltage	V _{EC}	I _E = 30A, V _{GE} = 0V	—	—	2.8	Volts	
Reverse Recovery Time	t _{rr}	I _E = 30A, V _{GE} = 0V,	—	—	110	nS	
Reverse Recovery Charge	Q _{rr}	di _E /dt = -60A/μs	—	0.08	—	μC	
Thermal Resistance (Junction-to-Fin)	R _{th(j-f)}	Per IGBT	—	—	1.9	°C/W	
		Per FWDi	—	—	2.4	°C/W	

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